

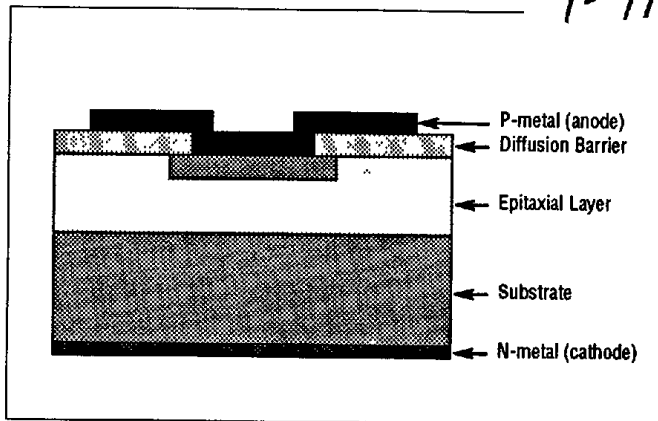
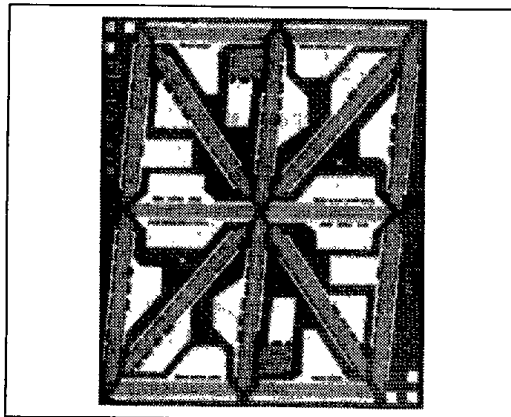
SIEMENS

**RM-81B
Mask-Diffused GaAsP
Monolithic LED**

Custom
Optoelectronic
Products

PART NO. 2680-0056

T-41-99



DESCRIPTION

Siemens RM-81B is a mask-diffused GaAsP monolithic light-emitting diode. With a bright and uniform 655 nm emission, this device is ideal for display applications.

MATERIAL

Epitaxial Layer: GaAs_{1-x}P_x : Te
 Substrate: GaAs : Si or GaAs : Te
 Metalizations: Anode Aluminum
 Cathode Gold-Germanium

Dimensions

(center to center): Height 0.135"
 Width 0.112"
 Thickness 0.010"

TYPICAL DEVICE PARAMETERS

| | | | |
|---|-----------|--------------|---------------|
| Forward I-V Characteristics | V_{F3} | 1.59 V | @ 20 mA |
| | V_{F2} | 1.57 V | @ 10 mA |
| | V_{F1} | 1.40 V | @ 100 μ A |
| Reverse I-V Characteristics | V_{R1} | -23.0 V | @ -10 μ A |
| Peak EL Wavelength | λ | 655 nm | @ 20 mA |
| Spectral Half-Width | FWHM | 40 nm | @ 20 mA |
| Luminous Intensity (Device does not have AR coating) | LI | 220 μ Cd | @ 10 mA |